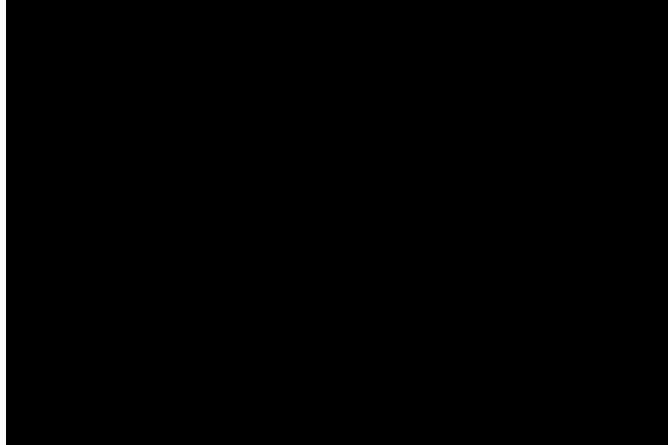
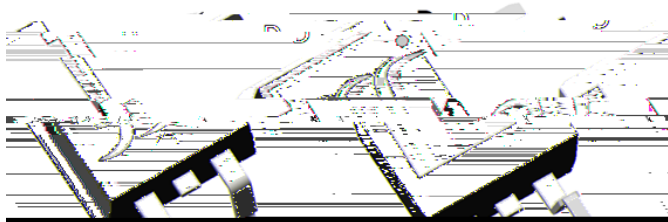




YJB17C80HJ

N-Channel Enhancement Mode Field Effect Transistor



Product Summary

• V_{DS}	800V
• I_D	17A
• $R_{DS(ON)}$ (at $V_{GS}=10V$)	290m Ω
• 100% EAS Tested	
• 100% V_{DS} Tested	

General Description

- Super Junction High Voltage MOSFET technology
- Low Power Loss by High Speed Switching and Low On-Resistance
- Moisture Sensitivity Level 1
- Epoxy Meets UL 94 V-0 Flammability Rating
- Halogen Free

Applications

- Power switching application
- Flyback power supply stages
- Adapter
- Lighting

■ Absolute Maximum Ratings ($T_A=25$ unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-source Voltage		V_{DS}	800	V
Gate-source Voltage		V_{GS}	± 30	V
Drain Current	$T_A=25$	I_D	2	A
	$T_A=100$		1.3	
	$T_C=25$		17	
	$T_C=100$		10	
Pulsed Drain Current ^A		I_{DM}	50	A
Avalanche energy ^B		EAS	225	mJ
Total Power Dissipation ^C	$T_A=25$	P_D	2.7	W
	$T_A=100$		1	
	$T_C=25$		200	
	$T_C=100$		80	
Junction and Storage Temperature Range		T_J, T_{STG}	-55 +150	

■ Thermal resistance

Parameter		Symbol	Typ	Max	Units
Thermal Resistance Junction-to-Ambient ^D	Steady-State	$R_{\theta JA}$	35	45	/W
Thermal Resistance Junction-to-Case	Steady-State	$R_{\theta JC}$	0.5	0.62	

■ Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJB17C80HJ	F2	YJB17C80HJ	800	/	8000	13" reel



YJB17C80HJ

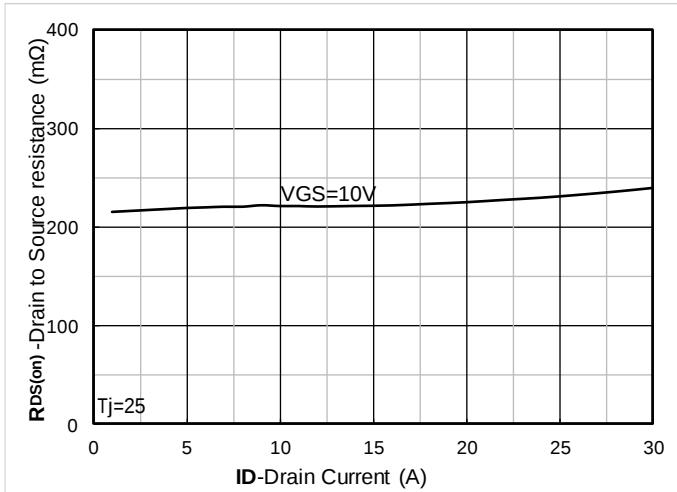


Figure7. $R_{DS(on)}$ VS Drain Current

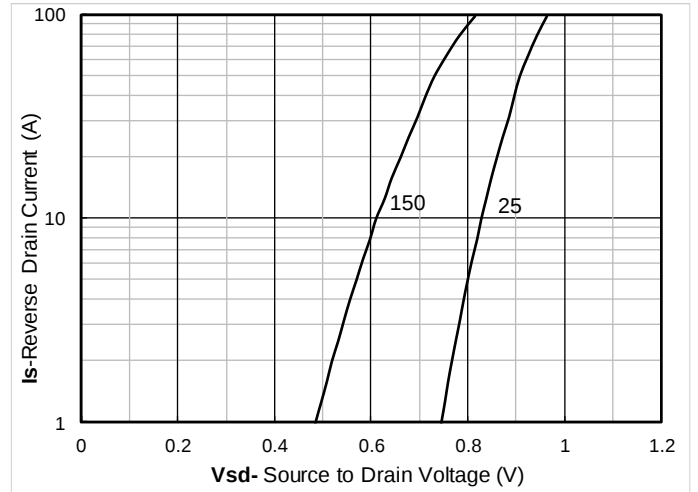


Figure8. Forward characteristics of reverse diode

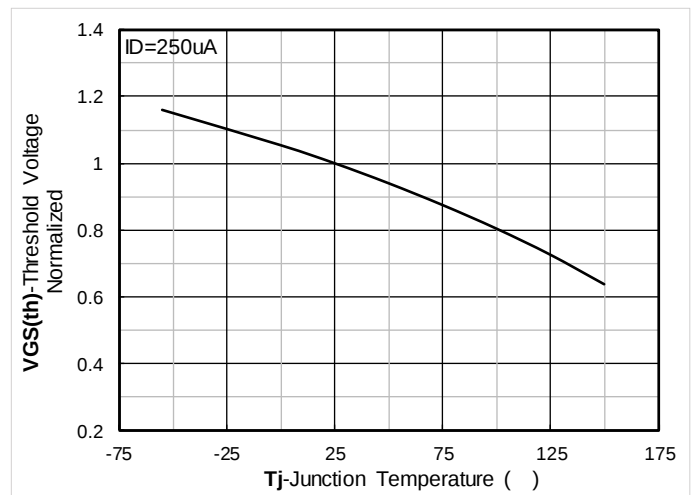


Figure10. Normalized Threshold voltage

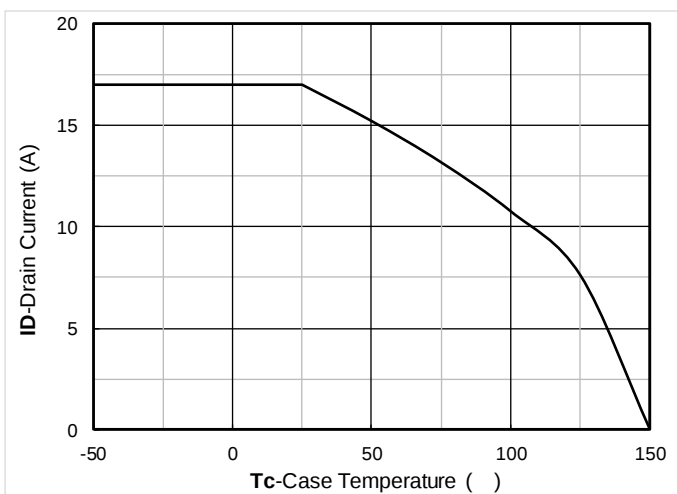


Figure11. Current dissipation

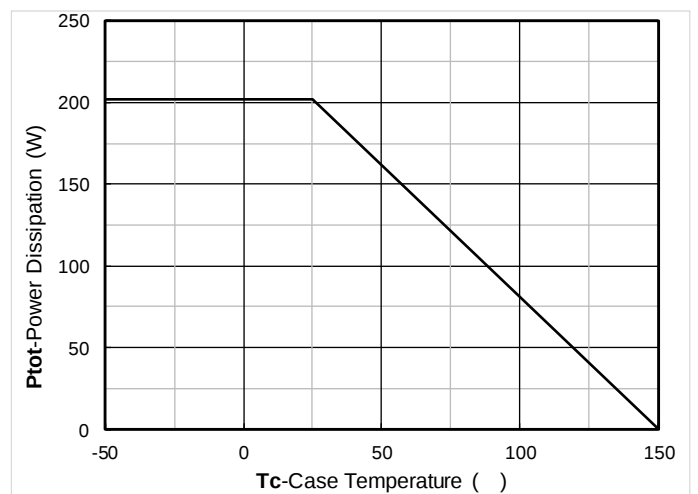


Figure12. Power dissipation



■TO-263-HY Package information

SYM.	MIN.	
A2		
b2		0.050
c		
c2		
D2		
E		
E1		

